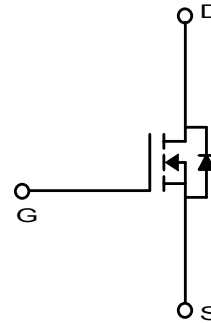
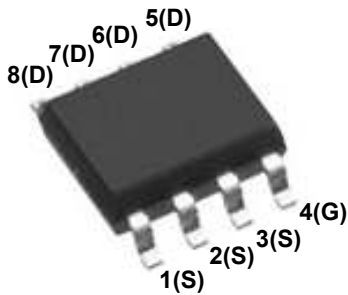


### General Description

The MDS1526 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDS1526 is suitable for DC/DC converter and general purpose applications.

### Features

- $V_{DS} = 30V$
- $I_D = 16.1A @ V_{GS} = 10V$
- $R_{DS(ON)} < 11.0m\Omega @ V_{GS} = 10V$   
 $< 16.4m\Omega @ V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$T_C=25^\circ C$	$I_D$	16.1	A
	$T_C=70^\circ C$		12.8	
	$T_A=25^\circ C$		11.3 <sup>(3)</sup>	
	$T_A=70^\circ C$		9.1 <sup>(3)</sup>	
Pulsed Drain Current		$I_{DM}$	40	A
Power Dissipation	$T_C=25^\circ C$	$P_D$	5.0	W
	$T_C=70^\circ C$		3.2	
	$T_A=25^\circ C$		2.5 <sup>(3)</sup>	
	$T_A=70^\circ C$		1.6 <sup>(3)</sup>	
Single Pulse Avalanche Energy <sup>(2)</sup>		$E_{AS}$	38	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	°C

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	24.6	

## Ordering Information

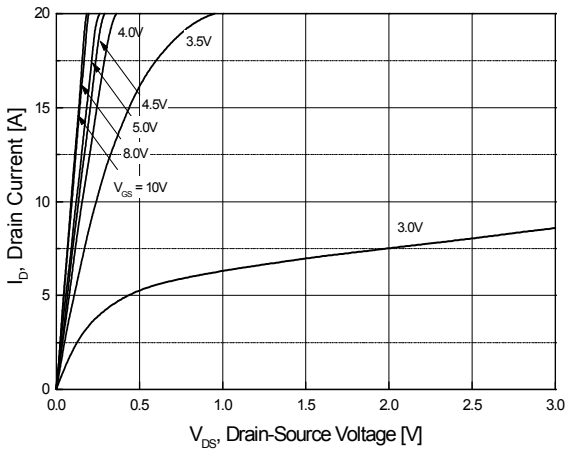
Part Number	Temp. Range	Package	Packing	Quantity	Rohs Status
MDS1526URH	-55~150°C	SOIC-8	Tape & Reel	3000 units	Halogen Free

## Electrical Characteristics (T<sub>J</sub> = 25°C)

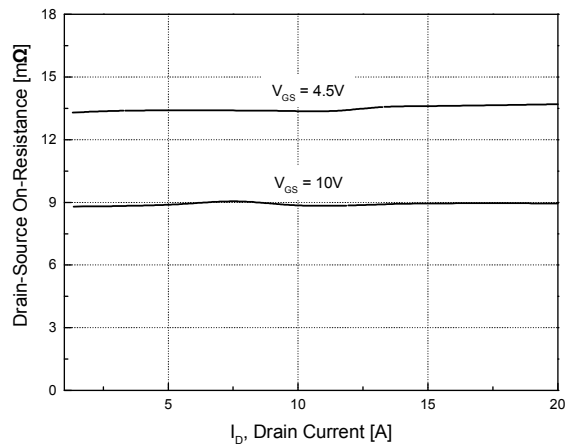
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.3	1.9	2.7	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	-	-	1	μA
		T <sub>J</sub> =55°C	-	-	5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±0.1	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A	-	9.6	11.0	mΩ
		T <sub>J</sub> =125°C	-	13.9	16.0	
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A	-	13.7	16.4	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 9A	-	22	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>DS</sub> = 15.0V, I <sub>D</sub> = 9A, V <sub>GS</sub> = 10V	7.8	11.2	14.5	nC
Total Gate Charge	Q <sub>g(4.5V)</sub>		3.8	5.4	7.0	
Gate-Source Charge	Q <sub>gs</sub>		-	2.0	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.8	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15.0V, V <sub>GS</sub> = 0V, f = 1.0MHz	485	692	900	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		47	68	88	
Output Capacitance	C <sub>oss</sub>		97	139	180	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15.0V, I <sub>D</sub> = 9A, R <sub>G</sub> = 3.0Ω	-	5.9	-	ns
Rise Time	t <sub>r</sub>		-	4.0	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	18.6	-	
Fall Time	t <sub>f</sub>		-	8.6	-	
Gate Resistance	R <sub>g</sub>	f=1 MHz	0.5	1.7	3.0	Ω
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 9A, V <sub>GS</sub> = 0V	-	0.83	1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 9A, di/dt = 100A/μs	-	17.8	26.7	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	8.9	13.3	nC

Note :

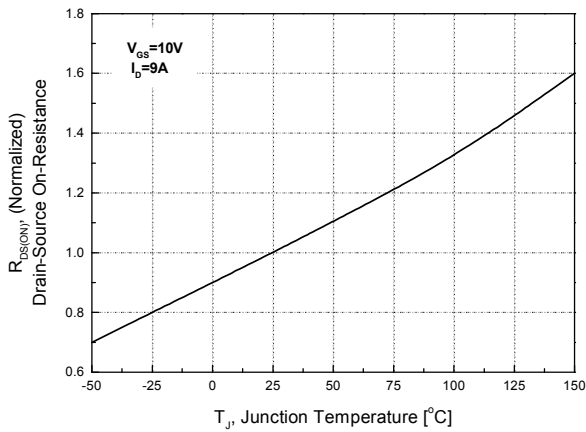
- Surface mounted FR-4 board by JEDEC (jesd51-7)
- E<sub>AS</sub> is tested at starting T<sub>J</sub> = 25°C, L = 0.1mH, I<sub>AS</sub> = 14.8A, V<sub>DD</sub> = 27V, V<sub>GS</sub> = 10V.
- T < 10sec



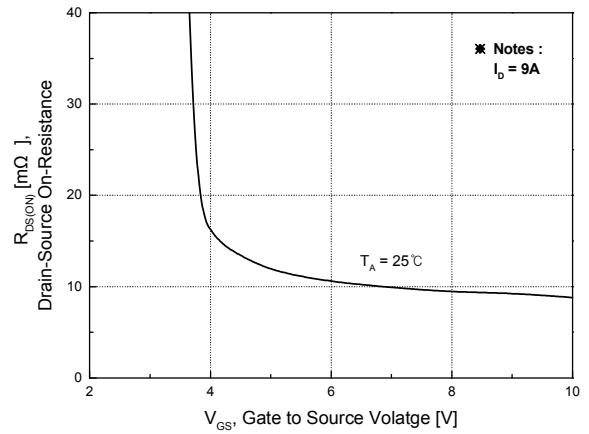
**Fig.1 On-Region Characteristics**



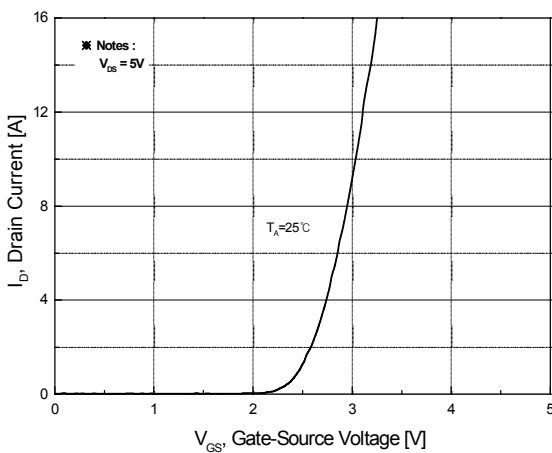
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



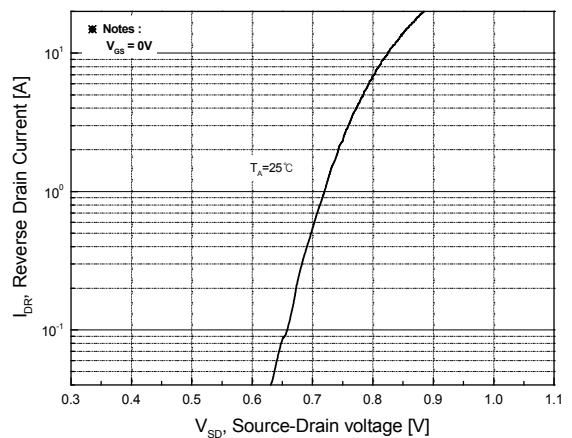
**Fig.3 On-Resistance Variation with Temperature**



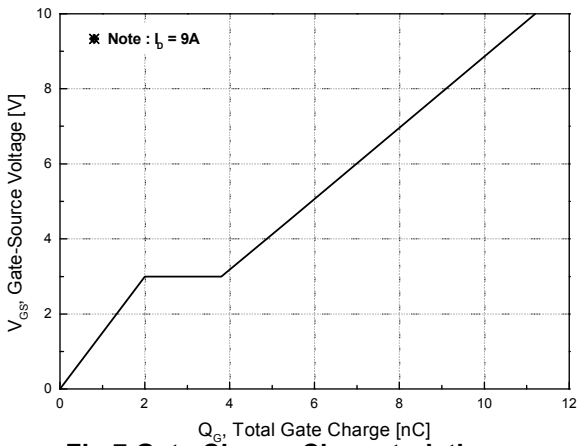
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



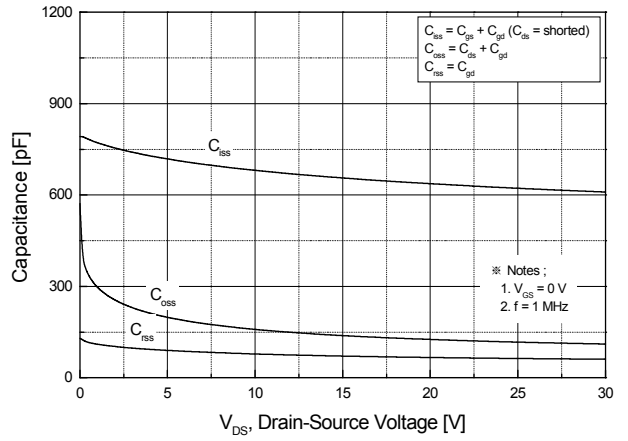
**Fig.5 Transfer Characteristics**



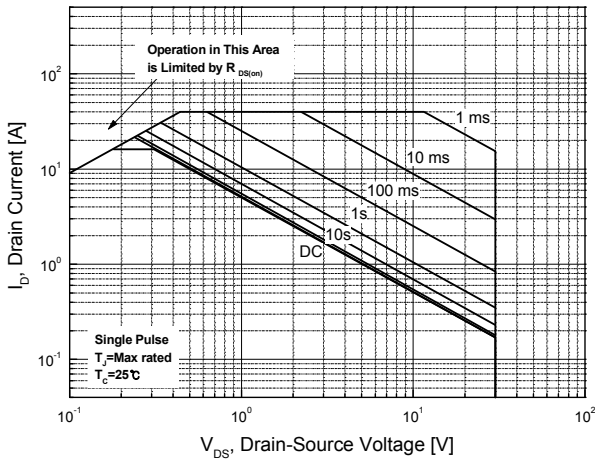
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



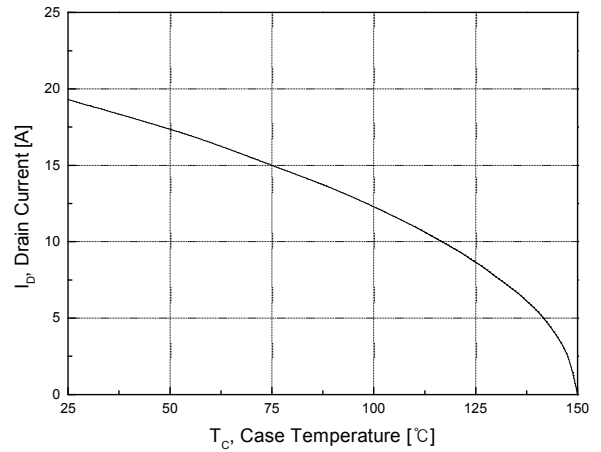
**Fig.7 Gate Charge Characteristics**



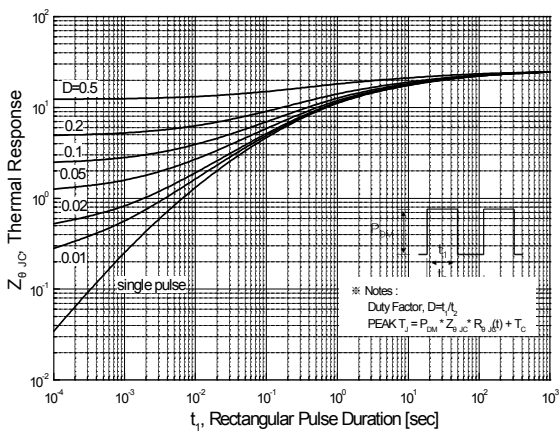
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Case Temperature**

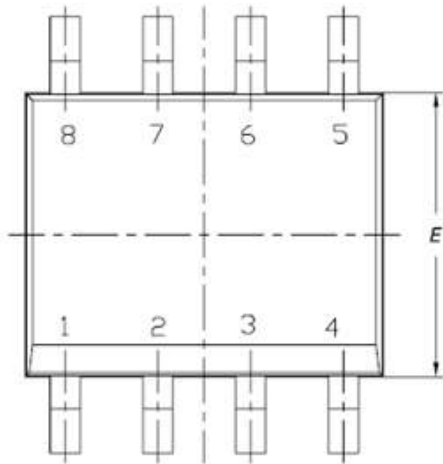


**Fig.11 Transient Thermal Response Curve**

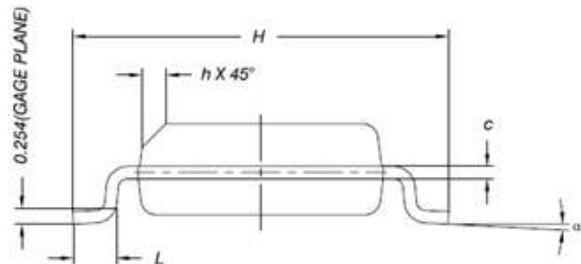
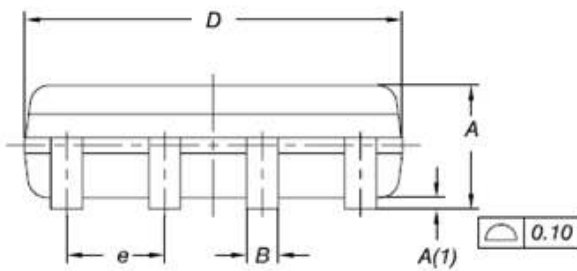
## Physical Dimensions

### 8 Leads, SOIC

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	-	-	1.75
A(1)	0.10	-	0.25
B	0.31	-	0.51
C	0.10	-	0.25
D	4.9 BSC		
E	3.9 BSC		
e	1.27 BSC		
H	6.0 BSC		
L	0.40	-	1.27
a	0	-	8
h	0.250	-	0.500
L2(Gage plane)	0.25 BSC		



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